

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE3407A uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -30V, I_{D} = -4.3A$

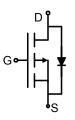
 $R_{DS(ON)}$ < 90m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ <55m Ω @ V_{GS} =-10V

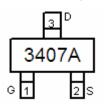
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3407A	NCE3407A	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-4.3	А
Drain Current-Pulsed (Note 1)	I _{DM}	-20	А
Maximum Power Dissipation	P _D	1.5	W
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	84	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V,V _{GS} =0V	-	-	-1	μΑ

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GSS GS(th)	V_{GS} =±20V, V_{DS} =0V	-	Typ -	±100	nA
GS(th)					IIA
GS(th)	1				
(-)	$V_{DS}=V_{GS},I_{D}=-250\mu A$	-1	-1.5	-3	V
R _{DS(ON)}	V _{GS} =-10V, I _D =-4.1A	-	42	55	mΩ
	V _{GS} =-4.5V, I _D =-4A	-	50	90	mΩ
g _{FS}	V _{DS} =-5V,I _D =-4.1A	5.5	-	-	S
Clss	\/ - 45\/\/ -0\/	-	700	-	PF
Coss	, , , , ,	-	120	-	PF
Crss	r=1.0lvinz	-	75	-	PF
d(on)		-	9	-	nS
t _r	V _{DD} =-15V,R _L =3.6Ω	-	5	-	nS
d(off)	V_{GS} =-10V, R_{GEN} =3 Ω	-	28	-	nS
t _f		-	13.5	-	nS
Qg		-	14	-	nC
Q _{gs}	V _{DS} =-15V,I _D =-4A,V _{GS} =-10V	-	3.1	-	nC
Q_{gd}		-	3	-	nC
		•			
/ _{SD}	V _{GS} =0V,I _S =-4.3A	-	-	-1.2	V
	OS(ON) GFS Clss Coss Crss d(on) tr	$\begin{array}{c} V_{GS} \!\!=\!\! -10 V, I_D \!\!=\!\! -4.1 A \\ V_{GS} \!\!=\!\! -4.5 V, I_D \!\!=\!\! -4 A \\ V_{DS} \!\!=\!\! -5 V, I_D \!\!=\!\! -4 A \\ V_{DS} \!\!=\!\! -5 V, I_D \!\!=\!\! -4.1 A \\ \end{array}$	$\begin{array}{c} V_{GS} = -10V, \ I_{D} = -4.1A \\ V_{GS} = -4.5V, \ I_{D} = -4A \\ \end{array} \\ \begin{array}{c} V_{DS} = -5V, I_{D} = -4A \\ \end{array} \\ \begin{array}{c} V_{DS} = -5V, I_{D} = -4A \\ \end{array} \\ \begin{array}{c} V_{DS} = -5V, I_{D} = -4A \\ \end{array} \\ \begin{array}{c} V_{DS} = -15V, V_{GS} = 0V, \\ V_{DS} = -15V, V_{D} = -4A, V_{D} = -15V, V_{D$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production

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Typical Electrical and Thermal Characteristics

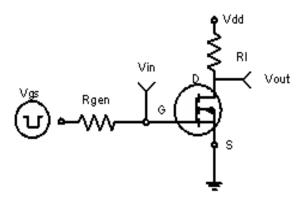


Figure 1:Switching Test Circuit

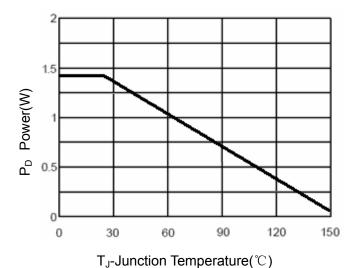


Figure 3 Power Dissipation

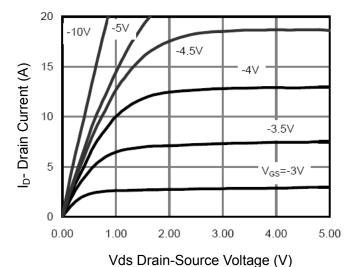


Figure 5 Output Characteristics

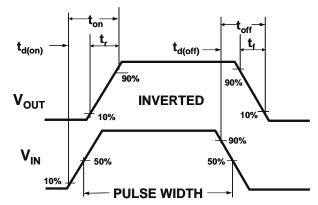


Figure 2:Switching Waveforms

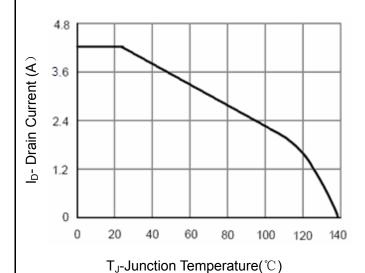


Figure 4 Drain Current

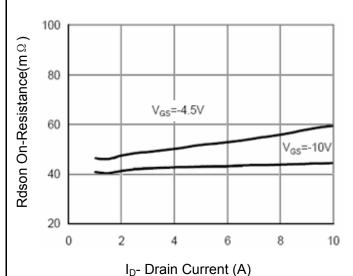


Figure 6 Drain-Source On-Resistance

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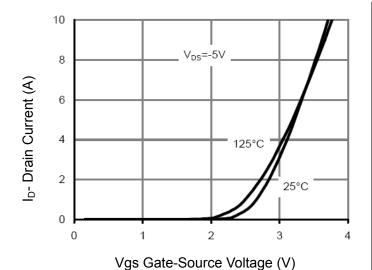
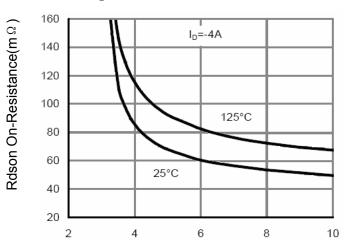


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

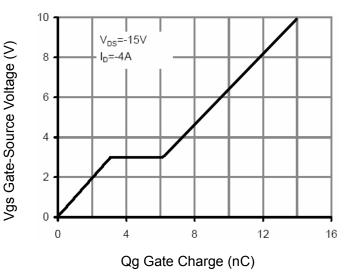


Figure 11 Gate Charge

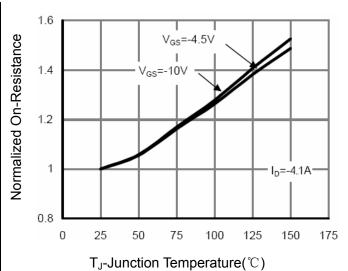


Figure 8 Drain-Source On-Resistance

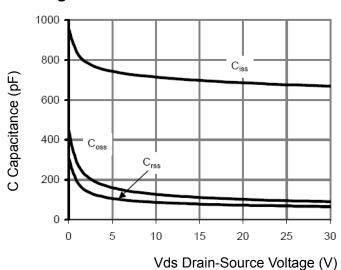


Figure 10 Capacitance vs Vds

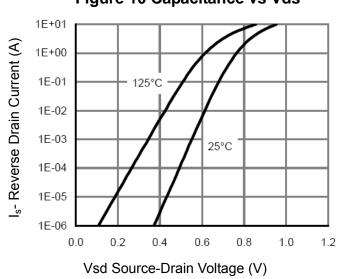


Figure 12 Source- Drain Diode Forward

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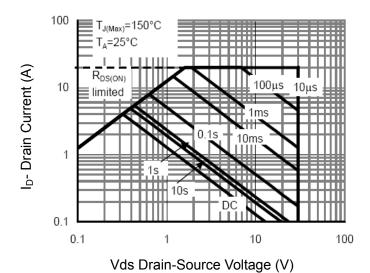


Figure 13 Safe Operation Area

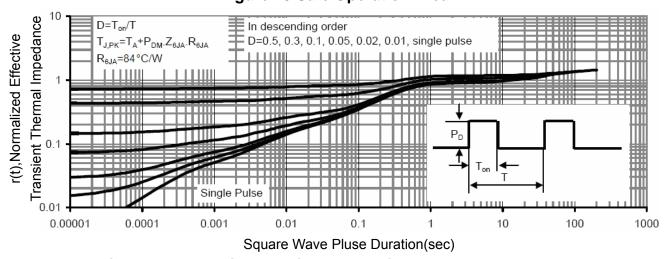
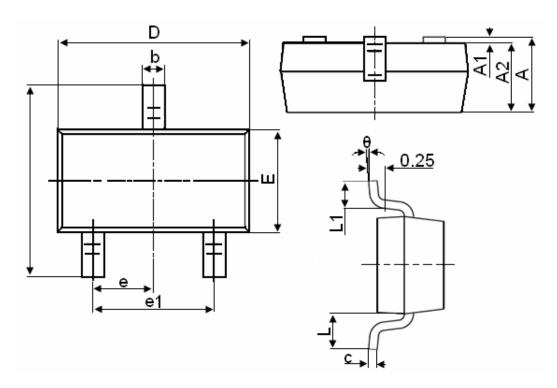


Figure 14 Normalized Maximum Transient Thermal Impedance

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SOT-23 Package Information



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
Е	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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